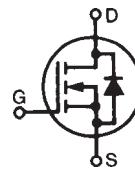
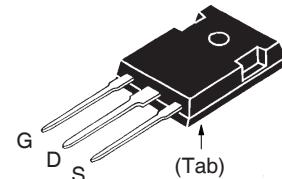


**Linear™ Power MOSFET
w/Extended FBSOA**
IXTH2N150L
 $V_{DSS} = 1500V$
 $I_{D25} = 2A$
 $R_{DS(on)} \leq 15\Omega$

N-Channel Enhancement Mode
Guaranteed FBSOA
Avalanche Rated



TO-247


 G = Gate D = Drain
 S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	1500	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$	1500	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ C$	2	A
I_{DM}	$T_C = 25^\circ C$, Pulse Width Limited by T_{JM}	6	A
P_D	$T_C = 25^\circ C$	290	W
T_J		-55 to +150	$^\circ C$
T_{JM}		+150	$^\circ C$
T_{stg}		-55 to +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	Plastic Body for 10s	260	$^\circ C$
M_d	Mounting Torque (TO-247)	1.13 / 10	Nm/lb.in
Weight		6	g

Features

- Designed for Linear Operation
- International Standard Package
- Avalanche Rated
- Guaranteed FBSOA at $75^\circ C$

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- DC Choppers
- DC-DC Converters
- Battery Chargers
- Programmable Loads
- Current Regulators
- Temperature and Lighting Controls

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 250\mu A$	1500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	6.0		V
I_{GSS}	$V_{GS} = \pm 30V$, $V_{DS} = 0V$		± 100	nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ C$		15	μA
			150	μA
$R_{DS(on)}$	$V_{GS} = 20V$, $I_D = 0.5 \cdot I_{D25}$, Note 1		15	Ω

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 20\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1	0.4	0.7	S
C_{iss}		1470		pF
C_{oss}		92		pF
C_{rss}		30		pF
$t_{d(on)}$		33		ns
t_r		55		ns
$t_{d(off)}$		85		ns
t_f	Resistive Switching Times $V_{GS} = 15\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 10\Omega$ (External)	84		ns
$Q_{g(on)}$		72		nc
Q_{gs}		15		nc
Q_{gd}		30		nc
R_{thJC}			0.43 $^\circ\text{C}/\text{W}$	
R_{thCS}		0.21		$^\circ\text{C}/\text{W}$

Safe Operating Area Specification

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
SOA	$V_{DS} = 1200\text{V}$, $I_D = 0.10\text{A}$, $T_C = 75^\circ\text{C}$, $T_p = 5\text{s}$	120		W

Source-Drain Diode

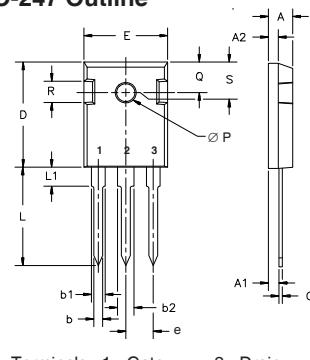
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_s	$V_{GS} = 0\text{V}$		2	A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}		8	A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{V}$, Note 1		1.5	V
t_{rr}		1.86		μs
I_{RM}		24		A
Q_{RM}	$I_F = 2\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$, $V_R = 100\text{V}$, $V_{GS} = 0\text{V}$	22		μC

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

TO-247 Outline



Dim.	Millimeter Min. Max.	Inches Min. Max.
A	4.7 5.3	.185 .209
A ₁	2.2 2.54	.087 .102
A ₂	2.2 2.6	.059 .098
b	1.0 1.4	.040 .055
b ₁	1.65 2.13	.065 .084
b ₂	2.87 3.12	.113 .123
C	.4 .8	.016 .031
D	20.80 21.46	.819 .845
E	15.75 16.26	.610 .640
e	5.20 5.72	.205 .225
L	19.81 20.32	.780 .800
L1	4.50	.177
OP	3.55 3.65	.140 .144
Q	5.89 6.40	.232 .252
R	4.32 5.49	.170 .216
S	6.15 BSC 242 BSC	.242 .242

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2 4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

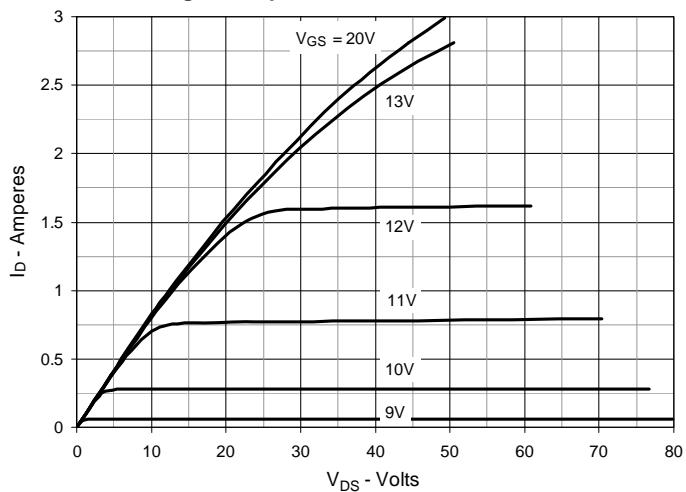
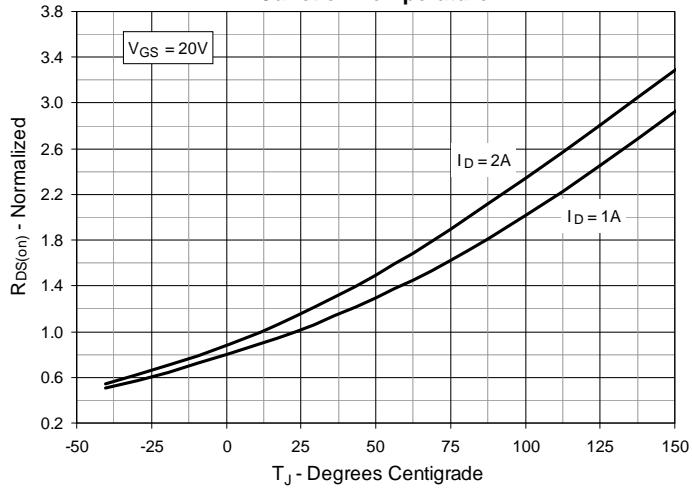
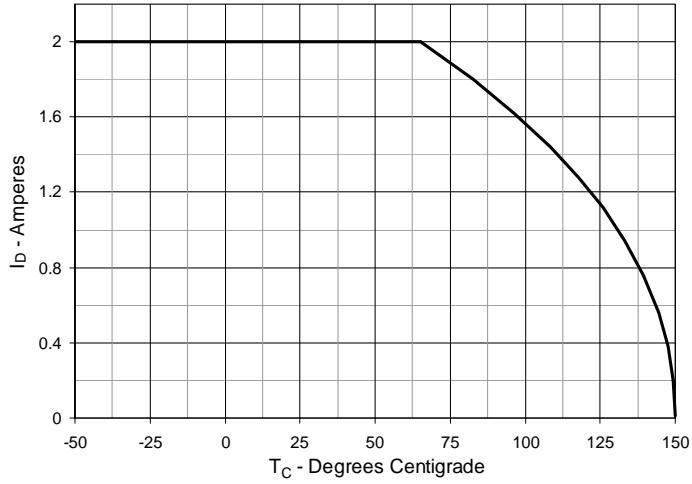
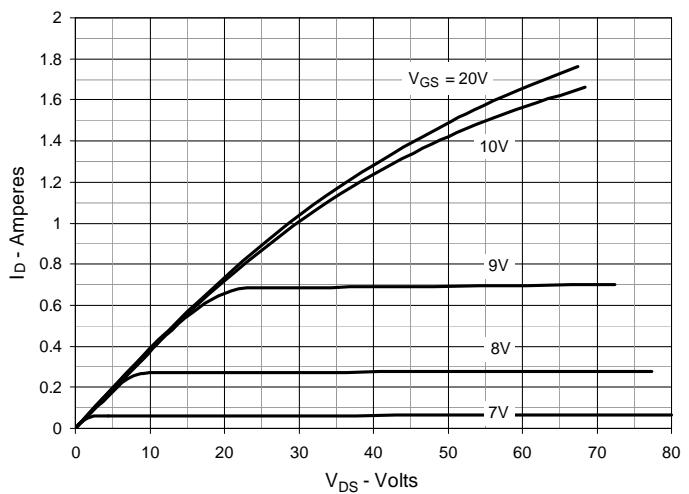
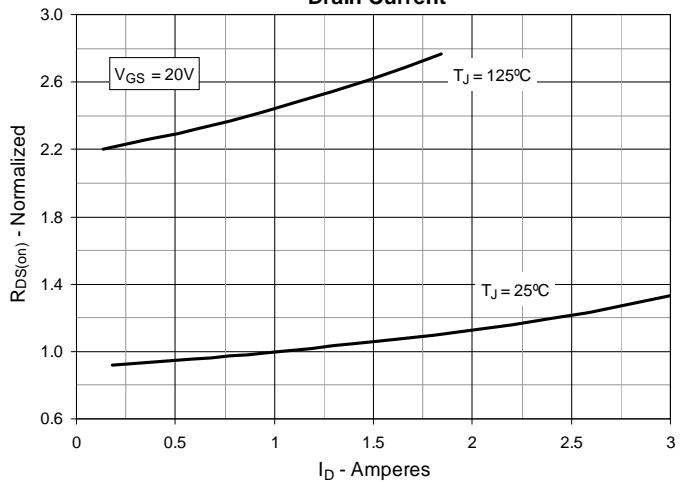
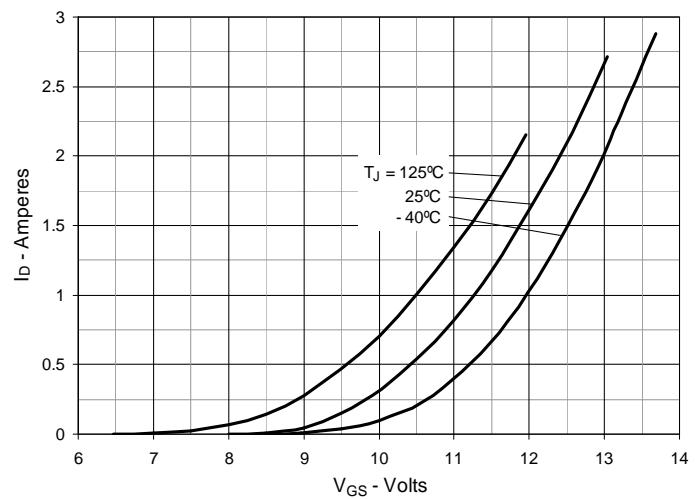
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$ **Fig. 3. $R_{DS(on)}$ Normalized to $I_D = 1\text{A}$ Value vs. Junction Temperature****Fig. 5. Maximum Drain Current vs. Case Temperature****Fig. 2. Output Characteristics @ $T_J = 125^\circ\text{C}$** **Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 1\text{A}$ Value vs. Drain Current****Fig. 6. Input Admittance**

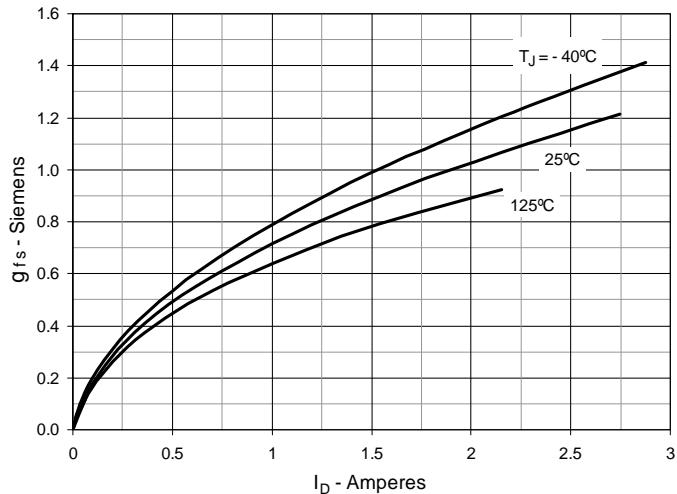
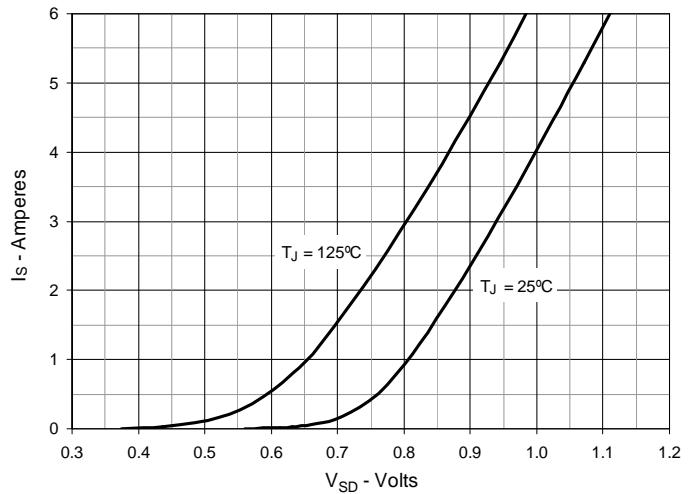
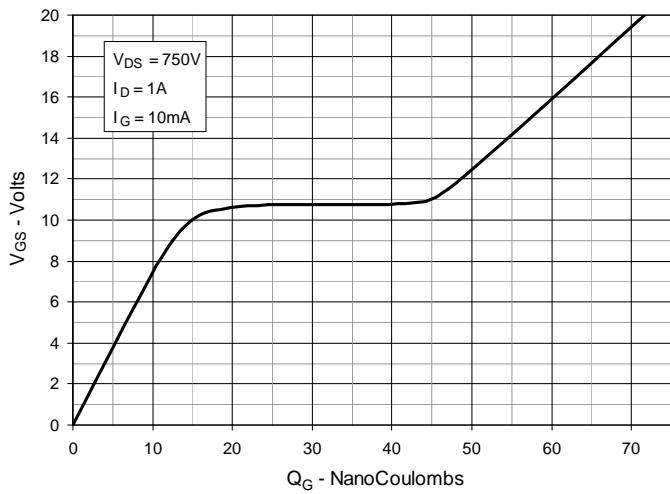
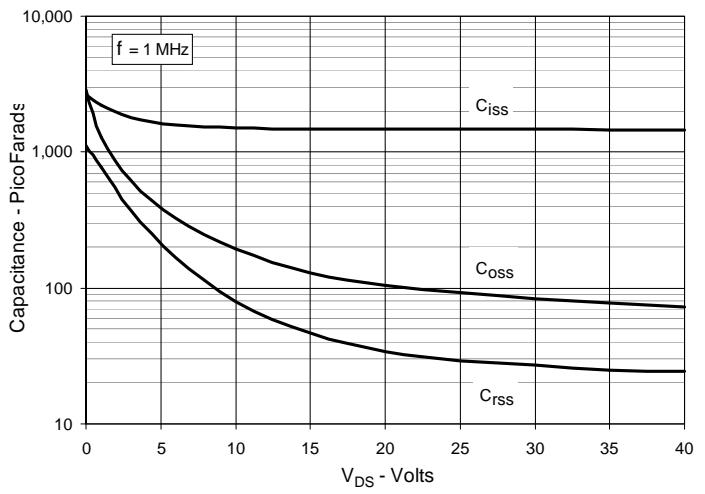
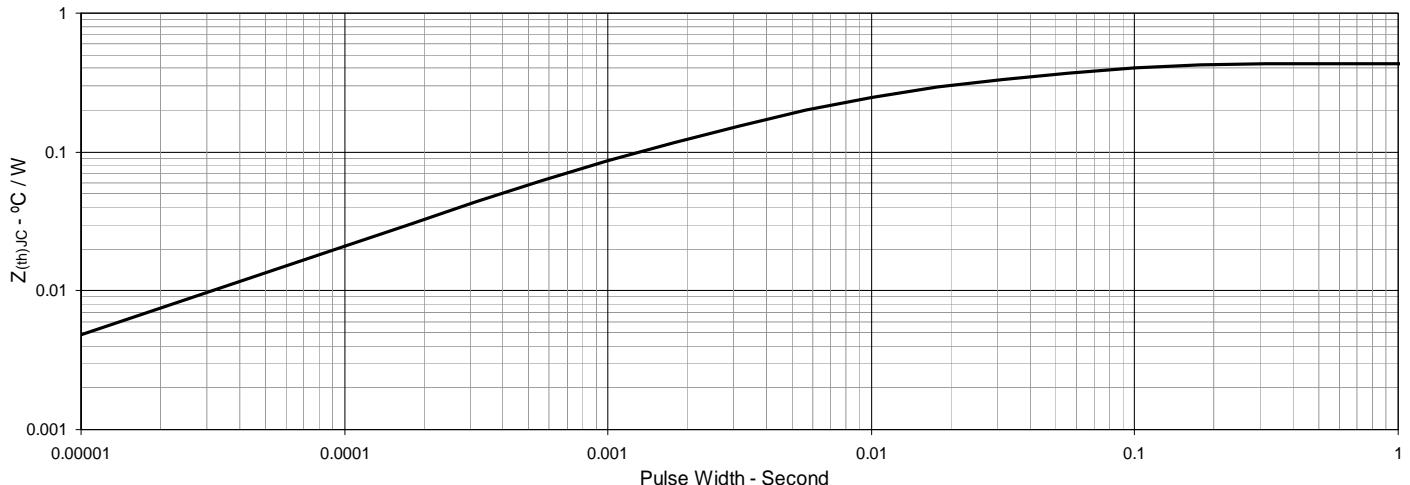
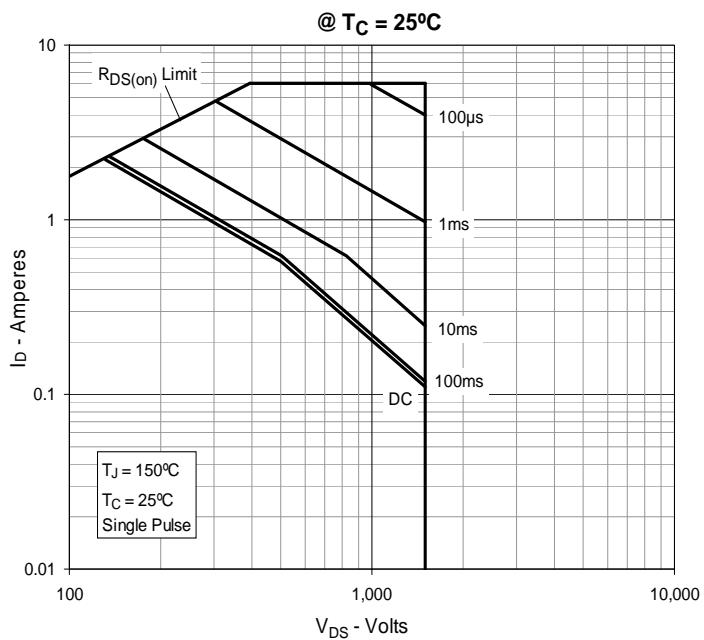
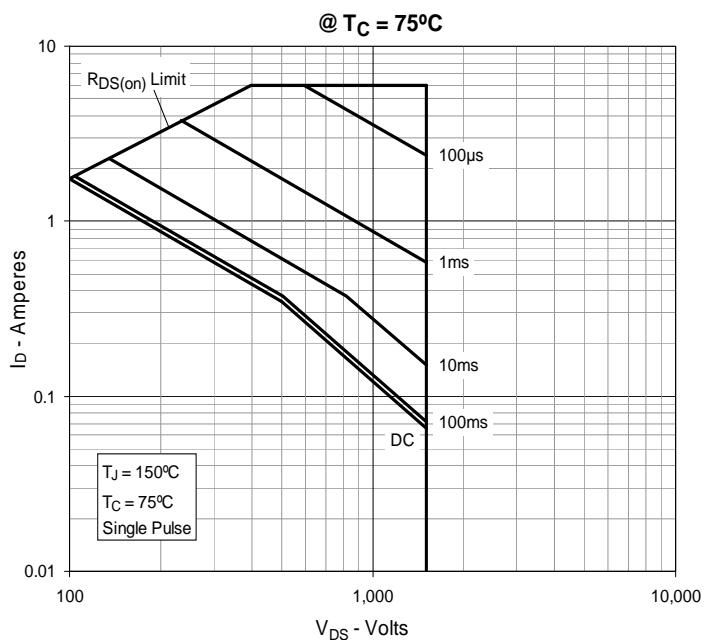
Fig. 7. Transconductance**Fig. 8. Forward Voltage Drop of Intrinsic Diode****Fig. 9. Gate Charge****Fig. 10. Capacitance****Fig. 11. Maximum Transient Thermal Impedance**

Fig. 12. Forward-Bias Safe Operating Area**Fig. 13. Forward-Bias Safe Operating Area**

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